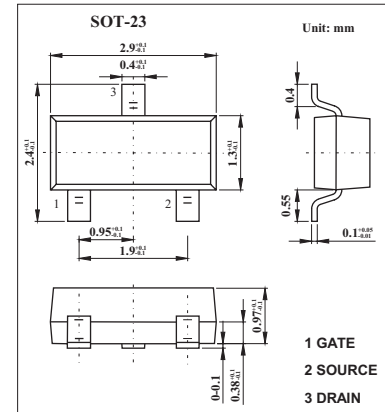


## MOS Fied Effect Transistor

### 2SJ203

#### ■ Features

- Directly driven by lcs having a 3V poer supply.
- Not necessary to consider driving current thanks to high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V <sub>GS</sub> =0	V <sub>DSS</sub>	-16	V
Gate to source voltage V <sub>DS</sub> =0	V <sub>GSS</sub>	±7	V
Drain current (DC)	I <sub>D</sub>	±200	mA
Drain current(pulse) *	I <sub>D</sub>	±400	mA
Power dissipation	P <sub>D</sub>	200	m W
Channel temperature	T <sub>ch</sub>	-55 to 80	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 ms; d ≤ 50%.

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0			-10	μ A
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±3V, V <sub>DS</sub> =0			±10	μ A
Gate cut-off voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-3V, I <sub>D</sub> =-1 μ A	-1.0	-1.6	-2.2	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =-3V, I <sub>D</sub> =-10mA	20	48		ms
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1mA		15	23	Ω
		V <sub>GS</sub> =-4.0V, I <sub>D</sub> =-1mA		7	10	Ω
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-3.0V, V <sub>GS</sub> =0, f=1MHZ		28		pF
Output capacitance	C <sub>oss</sub>			32		pF
Reverse transfer capacitance	C <sub>rss</sub>			6		pF
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS(on)</sub> =-3V, R <sub>G</sub> =10 Ω, V <sub>DS</sub> =-3.0V, I <sub>D</sub> =-10mA R <sub>L</sub> =300 Ω		180		ns
Rise time	t <sub>r</sub>			420		ns
Turn-off delay time	t <sub>d(off)</sub>			100		ns
Fall time	t <sub>f</sub>			200		ns

#### ■ Marking

Marking	H14
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